

METHOD OF FORMING A TRANSISTOR USING SELECTIVE EPITAXIAL GROWTH

Abstract

A method of forming a transistor involves firstly forming at least one gate structure on a semiconductor substrate. Then, a surface cleaning process is performed. In the surface cleaning process, a chemical oxidation method is utilized for forming a first oxide layer on a surface of the semiconductor substrate not covered with the gate structure and the first oxide layer is removed subsequently. Finally, a selective epitaxial growth method is utilized for forming a first epitaxial layer on the surface of the semiconductor substrate.